低消費電力SRAM 発注型名

R1 L V 5256 E SA - 5 S I #B1
R1 L P 04 08 D SP - 5 S I #B1
RM L V 04 16 E G SB - 4 S 2 #A A 1

RENESAS Memory

Chip configuration

L	LPSRAM, Single chip
W	LPSRAM, Two chips

Operating Voltage

V	3V
P	5V

Memory Density

5256	256Kb (x8)
01	1Mb
02	2Mb
04	4Mb
08	8Mb
16	16Mb
32	32Mb
64	64Mb

Bus Width

08	x8
16	x16

Chip Generation

Industrial Grade

Package Type

SA	TSOP-I (256Kb/8Mb/16Mb/32Mb/64Mb) sTSOP (1Mb/2Mb/4Mb)
SB	TSOP-II
SD	µTSOP
SF	TSOP-I (1Mb)
SP	SOP (256Kb, 4Mb)
SN	SOP (1Mb)
BG	FBGA

Access time

5	55 ns
4	45 ns

Stand-by current / Data retention current

S	Low power version
U	Ultra Low power version

Operating Temperature

R	0 ~ 70°C
I	-40 ~ 85°C
2	-40 ~ 85°C

Packing

A	Tray
C	Magazine
H	Tape & Reel (TSOP-II, µTSOP, SOP)
K	Tape & Reel (FBGA, TSOP-I, sTSOP)

Environment

A	Pb free (pure-Tin plating)
C	Pb free (non-pure-Tin plating)

Assembly Site Rev. , etc.

0	Rev. Code
1	Rev. Code

Packing, Environmental

	Packing	Environmental
#B0 / #B1	Tray or Magazine	Pb free
#S0 / #S1	Tape & Reel	Pb free

高速 4Mb SRAM 発注型名

R1 R W 04 16 D SB - 2 P I #D1

RENESAS Memory

Fast SRAM

Operation Voltage

W	3.3V
P	5V

Memory density

04	4Mb

Bus Width

08	x8
16	x16

Chip generation

Package type

GE	SOJ
SB	TSOP-II

Access time

2	12 ns
0	10 ns

Stand by current / Data retention current

P	Standard
L	Low power version
S	Super Low power version

Operating Temperature

R	0 ~ 70°C
I	-40 ~ 85°C

Packing, Environmental

	Packing	Environmental
#B0 / #B1	Magazine (SOJ)	Pb free
#D0 / #D1	Tray (TSOP)	Pb free
#S0 / #S1	Tape & Reel	Pb free

低消費電力SRAMラインアップ (256Kb)

Wafer Process	Density	Bit Org.	Catalog Part Name	Orderable Part Name	Package (pinout)	Packing Type	Access Time	Operating Voltage	Operating Temperature	PLP period
0.15µm Advanced	256Kbit	32K x 8	R1LP5256ESA-5SI	R1LP5256ESA-5SI#B1	TSOP-I (28)	Tray	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
				R1LP5256ESA-5SI#S1	TSOP-I (28)	Tape & Reel	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
			R1LP5256ESP-5SI	R1LP5256ESP-5SI#B1	SOP (28)	Magazine	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
				R1LP5256ESP-5SI#S1	SOP (28)	Tape & Reel	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
0.15µm Advanced	256Kbit	32K x 8	R1LV5256ESA-5SI	R1LV5256ESA-5SI#B1	TSOP-I (28)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				R1LV5256ESA-5SI#S1	TSOP-I (28)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			R1LV5256ESP-5SI	R1LV5256ESP-5SI#B1	SOP (28)	Magazine	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				R1LV5256ESP-5SI#S1	SOP (28)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032

（注）マガジン(Magazine)、チューブ(Tube)、スティック(Stick)と呼ばれる容器を、
ここではすべて「マガジン(Magazine) 」と表記します。

低消費電力SRAMラインアップ (1Mb~2Mb)

Wafer Process	Density	Bit Org.	Catalog Part Name	Orderable Part Name	Package (pinout)	Packing Type	Access Time	Operating Voltage	Operating Temperature	PLP period
0.15µm Advanced	1Mbit	128K x 8	R1LP0108ESA-5SI	R1LP0108ESA-5SI#B1	sTSOP (32)	Tray	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
				R1LP0108ESA-5SI#S1	sTSOP (32)	Tape & Reel	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
			R1LP0108ESF-5SI	R1LP0108ESF-5SI#B1	TSOP-I (32)	Tray	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Mar. 2031
				R1LP0108ESF-5SI#S1	TSOP-I (32)	Tape & Reel	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Mar. 2031
			R1LP0108ESN-5SI	R1LP0108ESN-5SI#B1	SOP (32)	Magazine	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
				R1LP0108ESN-5SI#S1	SOP (32)	Tape & Reel	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
0.15µm Advanced	1Mbit	128K x 8	R1LV0108ESA-5SI	R1LV0108ESA-5SI#B1	sTSOP (32)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				R1LV0108ESA-5SI#S1	sTSOP (32)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			R1LV0108ESF-5SI	R1LV0108ESF-5SI#B1	TSOP-I (32)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Mar. 2031
				R1LV0108ESF-5SI#S1	TSOP-I (32)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Mar. 2031
			R1LV0108ESN-5SI	R1LV0108ESN-5SI#B1	SOP (32)	Magazine	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				R1LV0108ESN-5SI#S1	SOP (32)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
0.15µm Advanced	2Mbit	256K x 8	R1LV0208BSA-5SI	R1LV0208BSA-5SI#B1	sTSOP (32)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				R1LV0208BSA-5SI#S1	sTSOP (32)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
		128K x16	R1LV0216BSB-5SI	R1LV0216BSB-5SI#B1	TSOP-II (44)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				R1LV0216BSB-5SI#S1	TSOP-II (44)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032

低消費電力SRAMラインアップ (4Mb)

Wafer Process	Density	Bit Org.	Catalog Part Name	Orderable Part Name	Package (pinout)	Packing Type	Access Time	Operating Voltage	Operating Temperature	PLP period
0.15µm Advanced	4Mbit	512K x 8	R1LP0408DSB-5SI	R1LP0408DSB-5SI#B1	TSOP-II (32)	Tray	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Mar. 2031
				R1LP0408DSB-5SI#S1	TSOP-II (32)	Tape & Reel	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Mar. 2031
			R1LP0408DSP-5SI	R1LP0408DSP-5SI#B1	SOP (32)	Magazine	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
				R1LP0408DSP-5SI#S1	SOP (32)	Tape & Reel	55ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
0.11µm Advanced	4Mbit	512K x 8	RMLV0408EGSA-4S2	RMLV0408EGSA-4S2#AA1	sTSOP (32)	Tray	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0408EGSA-4S2#KA1	sTSOP (32)	Tape & Reel	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			RMLV0408EGSB-4S2	RMLV0408EGSB-4S2#AA1	TSOP-II (32)	Tray	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Mar. 2031
				RMLV0408EGSB-4S2#HA1	TSOP-II (32)	Tape & Reel	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Mar. 2031
			RMLV0408EGSP-4S2	RMLV0408EGSP-4S2#CA1	SOP (32)	Magazine	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0408EGSP-4S2#HA1	SOP (32)	Tape & Reel	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
		256K x 16	RMLV0414EGSB-4S2	RMLV0414EGSB-4S2#AA1	TSOP-II (44)	Tray	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0414EGSB-4S2#HA1	TSOP-II (44)	Tape & Reel	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			RMLV0416EGBG-4S2	RMLV0416EGBG-4S2#AC0	FBGA (48)	Tray	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0416EGBG-4S2#KC0	FBGA (48)	Tape & Reel	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			RMLV0416EGSB-4S2	RMLV0416EGSB-4S2#AA1	TSOP-II (44)	Tray	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0416EGSB-4S2#HA1	TSOP-II (44)	Tape & Reel	45ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032

低消費電力SRAMラインアップ (8Mb)

Wafer Process	Density	Bit Org.	Catalog Part Name	Orderable Part Name	Package (pinout)	Packing Type	Access Time	Operating Voltage	Operating Temperature	PLP period
0.11µm Advanced	8Mbit	1M x 8	RMLV0808BGSB-4S2	RMLV0808BGSB-4S2#AA0	TSOP-II (44)	Tray	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0808BGSB-4S2#HA0	TSOP-II (44)	Tape & Reel	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
		512K x 16	RMLV0816BGBG-4S2	RMLV0816BGBG-4S2#AC0	FBGA (48)	Tray	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0816BGBG-4S2#KC0	FBGA (48)	Tape & Reel	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
		512K x 16 / 1M x 8	RMLV0816BGSA-4S2	RMLV0816BGSA-4S2#AA0	TSOP-I (48)	Tray	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0816BGSA-4S2#KA0	TSOP-I (48)	Tape & Reel	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
		512K x 16	RMLV0816BGSB-4S2	RMLV0816BGSB-4S2#AA0	TSOP-II (44)	Tray	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0816BGSB-4S2#HA0	TSOP-II (44)	Tape & Reel	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
		512K x 16 / 1M x 8	RMLV0816BGSD-4S2	RMLV0816BGSD-4S2#AA1	µTSOP (52)	Tray	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV0816BGSD-4S2#HA1	µTSOP (52)	Tape & Reel	45ns	2.4V ~ 3.6V	-40 ~ 85 °C	Dec. 2032

低消費電力SRAMラインアップ (16Mb)

Wafer Process	Density	Catalog Part Name	Orderable Part Name	Package (pinout)	Packing Type	Access Time	Standby Current (typ. / max.)	Operating Voltage	Operating Temperature	PLP period
RMLV1616A-U series 新製品		RMLV1616AGBG-4U2	RMLV1616AGBG-4U2#AC0	FBGA (48)	Tray	45ns	0.4µA / 8µA	2.7V ~ 3.6V	-40 ~ 85 °C	
			RMLV1616AGBG-4U2#KC0	FBGA (48)	Tape & Reel	45ns	0.4µA / 8µA	2.7V ~ 3.6V	-40 ~ 85 °C	
		RMLV1616AGBG-5U2	RMLV1616AGBG-5U2#AC0	FBGA (48)	Tray	55ns	0.4µA / 8µA	2.7V ~ 3.6V	-40 ~ 85 °C	
			RMLV1616AGBG-5U2#KC0	FBGA (48)	Tape & Reel	55ns	0.4µA / 8µA	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032 予定（注）
0.11µm Advanced	16Mbit	RMLV1616AGSA-4U2	RMLV1616AGSA-4U2#AA0	TSOP-I (48)	Tray	45ns	0.4µA / 8µA	2.7V ~ 3.6V	-40 ~ 85 °C	
			RMLV1616AGSA-4U2#KA0	TSOP-I (48)	Tape & Reel	45ns	0.4µA / 8µA	2.7V ~ 3.6V	-40 ~ 85 °C	
		RMLV1616AGSA-5U2	RMLV1616AGSA-5U2#AA0	TSOP-I (48)	Tray	55ns	0.4µA / 8µA	2.7V ~ 3.6V	-40 ~ 85 °C	
			RMLV1616AGSA-5U2#KA0	TSOP-I (48)	Tape & Reel	55ns	0.4µA / 8µA	2.7V ~ 3.6V	-40 ~ 85 °C	
RMLV1616A-S series 量産中		RMLV1616AGBG-5S2	RMLV1616AGBG-5S2#AC0	FBGA (48)	Tray	55ns	0.5µA / 16µA	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			RMLV1616AGBG-5S2#KC0	FBGA (48)	Tape & Reel	55ns	0.5µA / 16µA	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
0.11µm Advanced	16Mbit	RMLV1616AGSA-5S2	RMLV1616AGSA-5S2#AA0	TSOP-I (48)	Tray	55ns	0.5µA / 16µA	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			RMLV1616AGSA-5S2#KA0	TSOP-I (48)	Tape & Reel	55ns	0.5µA / 16µA	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
		RMLV1616AGSD-5S2	RMLV1616AGSD-5S2#AA1	µTSOP (52)	Tray	55ns	0.5µA / 16µA	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			RMLV1616AGSD-5S2#HA1	µTSOP (52)	Tape & Reel	55ns	0.5µA / 16µA	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032

注：RMLV1616A-Uシリーズは、他製品と同じPLP適用期間を登録予定です。

低消費電力SRAMラインアップ (32Mb~64Mb)

Wafer Process	Density	Bit Org.	Catalog Part Name	Orderable Part Name	Package (pinout)	Packing Type	Access Time	Operating Voltage	Operating Temperature	PLP period
0.11µm Advanced	32Mbit	2M x 16	RMWV3216AGBG-5S2	RMWV3216AGBG-5S2#AC0	FBGA (48)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMWV3216AGBG-5S2#KC0	FBGA (48)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
0.11µm Advanced	32Mbit	2M x 16	RMLV3216AGBG-5S2	RMLV3216AGBG-5S2#AC0	FBGA (48)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV3216AGBG-5S2#KC0	FBGA (48)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
		2M x 16 / 4M x 8	RMLV3216AGSA-5S2	RMLV3216AGSA-5S2#AA0	TSOP-I (48)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV3216AGSA-5S2#KA0	TSOP-I (48)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			RMLV3216AGSD-5S2	RMLV3216AGSD-5S2#AA0	µTSOP (52)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMLV3216AGSD-5S2#HA0	µTSOP (52)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
0.11µm Advanced	64Mbit	4M x 16	RMWV6416AGBG-5S2	RMWV6416AGBG-5S2#AC0	FBGA (48)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMWV6416AGBG-5S2#KC0	FBGA (48)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
		4M x 16 / 8M x 8	RMWV6416AGSA-5S2	RMWV6416AGSA-5S2#AA0	TSOP-I (48)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMWV6416AGSA-5S2#KA0	TSOP-I (48)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			RMWV6416AGSD-5S2	RMWV6416AGSD-5S2#AA0	µTSOP (52)	Tray	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				RMWV6416AGSD-5S2#HA0	µTSOP (52)	Tape & Reel	55ns	2.7V ~ 3.6V	-40 ~ 85 °C	Dec. 2032

高速SRAMラインアップ (4Mb, 5V)

Wafer Process	Density	Bit Org.	Catalog Part Name	Orderable Part Name	Package (pinout)	Packing Type	Access Time	Operating Voltage	Operating Temperature	PLP period
0.18µm CMOS	4Mbit	512K x 8	R1RP0408DGE-2LR	R1RP0408DGE-2LR#B1	SOJ (36)	Magazine	12ns	4.5V ~ 5.5V	0 ~ 70 °C	-
			R1RP0408DGE-2PI	R1RP0408DGE-2PI#B1	SOJ (36)	Magazine	12ns	4.5V ~ 5.5V	-40 ~ 85 °C	-
			R1RP0408DGE-2PR	R1RP0408DGE-2PR#B1	SOJ (36)	Magazine	12ns	4.5V ~ 5.5V	0 ~ 70 °C	-
		256K x 16	R1RP0416DGE-2LR	R1RP0416DGE-2LR#B1	SOJ (44)	Magazine	12ns	4.5V ~ 5.5V	0 ~ 70 °C	-
			R1RP0416DGE-2PI	R1RP0416DGE-2PI#B1	SOJ (44)	Magazine	12ns	4.5V ~ 5.5V	-40 ~ 85 °C	-
			R1RP0416DGE-2PR	R1RP0416DGE-2PR#B1	SOJ (44)	Magazine	12ns	4.5V ~ 5.5V	0 ~ 70 °C	-
			R1RP0416DGE-2SR	R1RP0416DGE-2SR#B1	SOJ (44)	Magazine	12ns	4.5V ~ 5.5V	0 ~ 70 °C	-
		256K x 16	R1RP0416DSB-0PI	R1RP0416DSB-0PI#D1	TSOP-II (44)	Tray	10ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
			R1RP0416DSB-0PR	R1RP0416DSB-0PR#D1	TSOP-II (44)	Tray	10ns	4.5V ~ 5.5V	0 ~ 70 °C	Dec. 2032
			R1RP0416DSB-2LR	R1RP0416DSB-2LR#D1	TSOP-II (44)	Tray	12ns	4.5V ~ 5.5V	0 ~ 70 °C	Dec. 2032
				R1RP0416DSB-2LR#S1	TSOP-II (44)	Tape & Reel	12ns	4.5V ~ 5.5V	0 ~ 70 °C	Dec. 2032
			R1RP0416DSB-2PI	R1RP0416DSB-2PI#D1	TSOP-II (44)	Tray	12ns	4.5V ~ 5.5V	-40 ~ 85 °C	Dec. 2032
			R1RP0416DSB-2PR	R1RP0416DSB-2PR#D1	TSOP-II (44)	Tray	12ns	4.5V ~ 5.5V	0 ~ 70 °C	Dec. 2032
				R1RP0416DSB-2PR#S1	TSOP-II (44)	Tape & Reel	12ns	4.5V ~ 5.5V	0 ~ 70 °C	Dec. 2032
			R1RP0416DSB-2SR	R1RP0416DSB-2SR#D1	TSOP-II (44)	Tray	12ns	4.5V ~ 5.5V	0 ~ 70 °C	Dec. 2032

高速SRAMラインアップ (4Mb, 3.3V)

Wafer Process	Density	Bit Org.	Catalog Part Name	Orderable Part Name	Package (pinout)	Packing Type	Access Time	Operating Voltage	Operating Temperature	PLP period
0.18µm CMOS	4Mbit	512K x 8	R1RW0408DGE-2LR	R1RW0408DGE-2LR#B1	SOJ (36)	Magazine	12ns	3.0V ~ 3.6V	0 ~ 70 °C	-
			R1RW0408DGE-2PI	R1RW0408DGE-2PI#B1	SOJ (36)	Magazine	12ns	3.0V ~ 3.6V	-40 ~ 85 °C	-
			R1RW0408DGE-2PR	R1RW0408DGE-2PR#B1	SOJ (36)	Magazine	12ns	3.0V ~ 3.6V	0 ~ 70 °C	-
		256K x 16	R1RW0416DGE-2LR	R1RW0416DGE-2LR#B1	SOJ (44)	Magazine	12ns	3.0V ~ 3.6V	0 ~ 70 °C	-
			R1RW0416DGE-2PI	R1RW0416DGE-2PI#B1	SOJ (44)	Magazine	12ns	3.0V ~ 3.6V	-40 ~ 85 °C	-
			R1RW0416DGE-2PR	R1RW0416DGE-2PR#B1	SOJ (44)	Magazine	12ns	3.0V ~ 3.6V	0 ~ 70 °C	-
		256K x 16	R1RW0416DSB-0PI	R1RW0416DSB-0PI#D1	TSOP-II (44)	Tray	10ns	3.0V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				R1RW0416DSB-0PI#S1	TSOP-II (44)	Tape & Reel	10ns	3.0V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			R1RW0416DSB-0PR	R1RW0416DSB-0PR#D1	TSOP-II (44)	Tray	10ns	3.0V ~ 3.6V	0 ~ 70 °C	Dec. 2032
				R1RW0416DSB-0PR#S1	TSOP-II (44)	Tape & Reel	10ns	3.0V ~ 3.6V	0 ~ 70 °C	Dec. 2032
			R1RW0416DSB-2LR	R1RW0416DSB-2LR#D1	TSOP-II (44)	Tray	12ns	3.0V ~ 3.6V	0 ~ 70 °C	Dec. 2032
			R1RW0416DSB-2PI	R1RW0416DSB-2PI#D1	TSOP-II (44)	Tray	12ns	3.0V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
				R1RW0416DSB-2PI#S1	TSOP-II (44)	Tape & Reel	12ns	3.0V ~ 3.6V	-40 ~ 85 °C	Dec. 2032
			R1RW0416DSB-2PR	R1RW0416DSB-2PR#D1	TSOP-II (44)	Tray	12ns	3.0V ~ 3.6V	0 ~ 70 °C	Dec. 2032
				R1RW0416DSB-2PR#S1	TSOP-II (44)	Tape & Reel	12ns	3.0V ~ 3.6V	0 ~ 70 °C	Dec. 2032
			R1RW0416DSB-2SR	R1RW0416DSB-2SR#D1	TSOP-II (44)	Tray	12ns	3.0V ~ 3.6V	0 ~ 70 °C	Dec. 2032